

27. The transistor structure of claim 18 wherein said silicide layer extends to said dielectric of increased thickness.

REMARKS

Claims 10 to 27 have been added. The main thrust of the added claims is to cover the wrap-around silicidation of the polysilicon gate which is nowhere taught or suggested by the cited references. This is in addition to the invention claimed in claims 8 and 9 as discussed in prior amendments and the combination of these features.

Action and allowance are respectfully requested.

Respectfully submitted,



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